

## 1. Scope

The present specifications shall apply to FMXK-1086S.

## 2. Outline

High Frequency Rectification

Type	Silicon Diode
Structure	Resin Molded
Applications	High Frequency Rectification,etc

## 3. Flammability

UL94V-0(Equivalent)

*Not Recommended for New Designs*

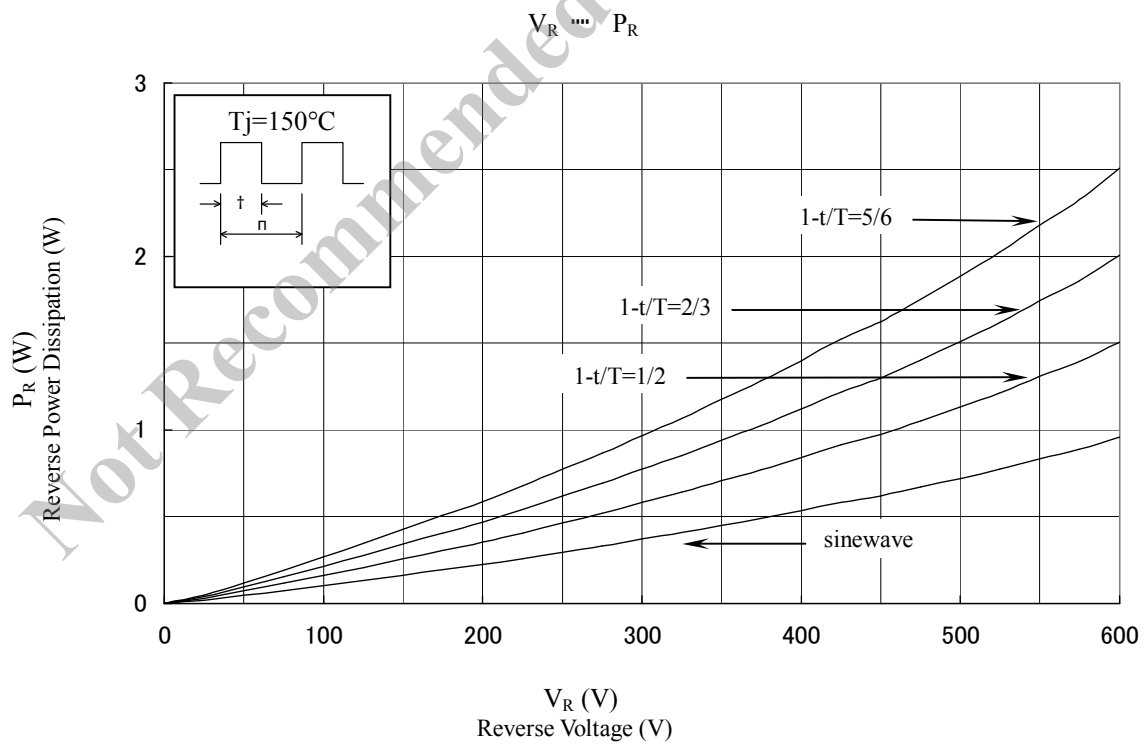
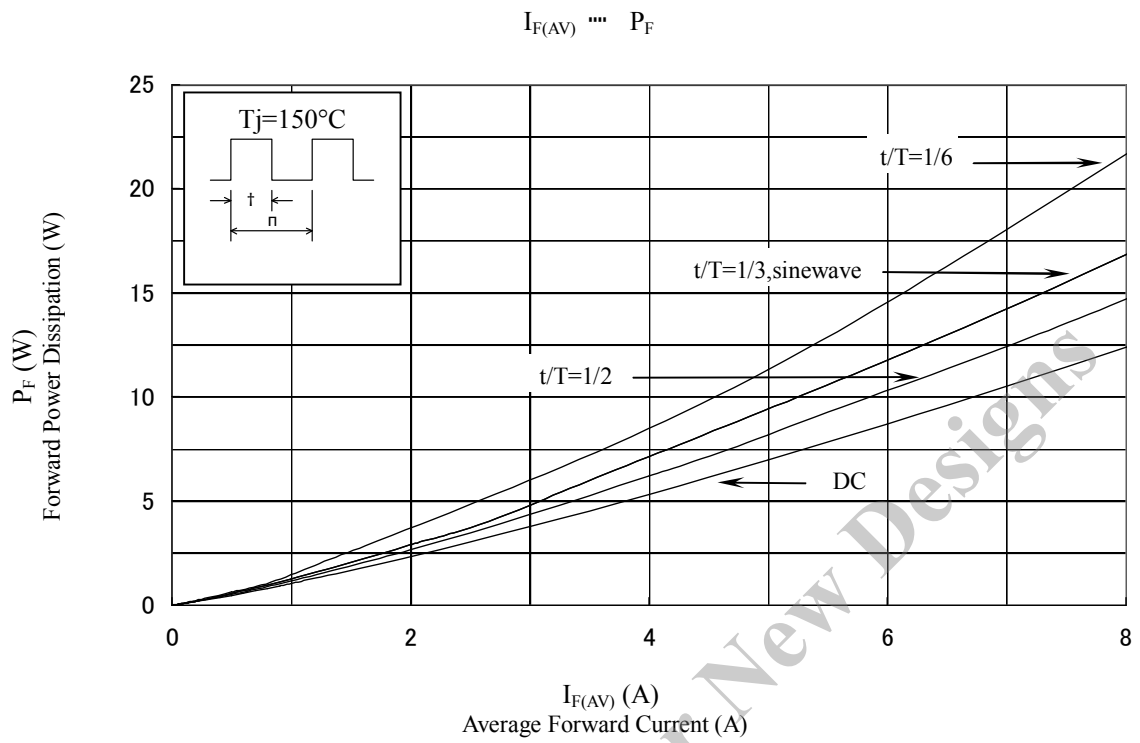
## 4. Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	$V_{RSM}$	V	600	
2	Peak Reverse Voltage	$V_{RM}$	V	600	
3	Average Forward Current	$I_{F(AV)}$	A	8	$T_c=76.0^{\circ}\text{C}(\text{c})$ Sinewave
4	Peak Surge Forward Current	$I_{FSM}$	A	100	10msec. Half sinewave, one shot
5	$I^2t$ Limiting Value	$I^2t$	$\text{A}^2\text{s}$	50	$1\text{msec} \leq t \leq 10\text{msec}$
6	Junction Temperature	$T_j$	$^{\circ}\text{C}$	-40~+150	
7	Storage Temperature	$T_{stg}$	$^{\circ}\text{C}$	-40~+150	

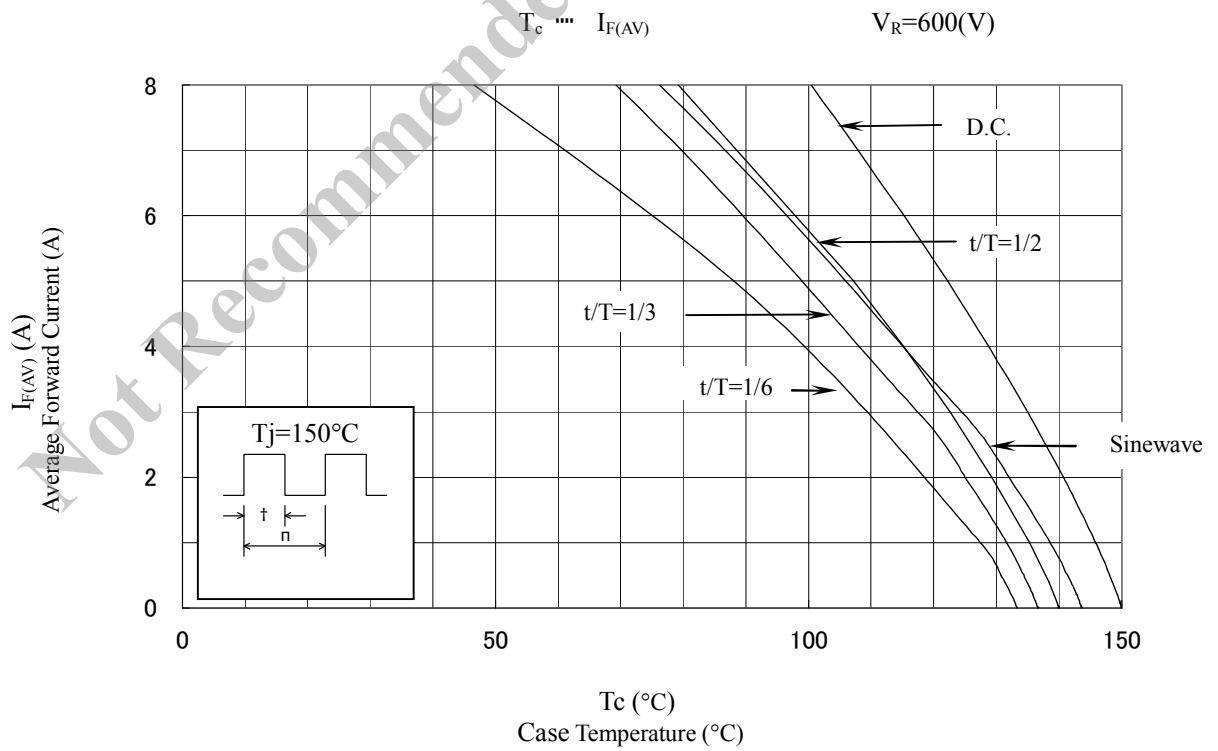
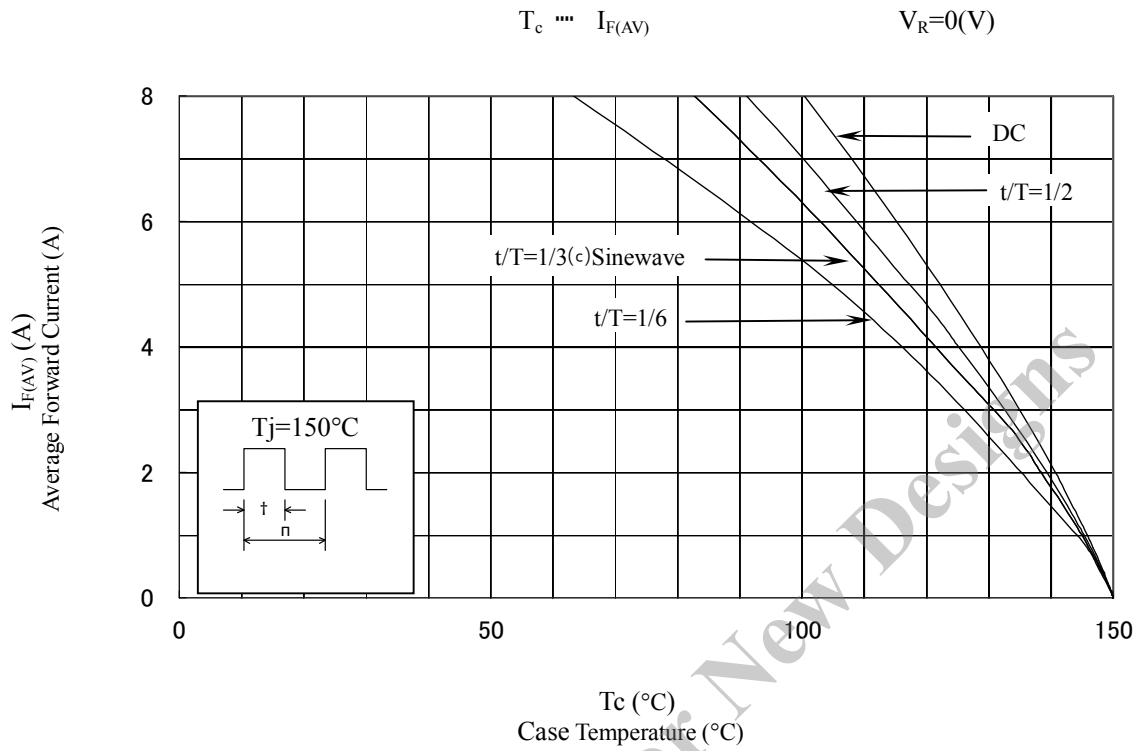
## 5. Electrical characteristics

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	$V_F$	V	1.75 max.	$I_F = \frac{1}{10} \text{ A}$
2	Reverse Leakage Current	$I_R$	$\mu\text{A}$	30 $\phi$ max.	$V_R = V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H^n I_R$	mA	6 max.	$V_R = V_{RM}, T_j = 150^{\circ}\text{C}$
4	Reverse Recovery Time	$t_{rr}$	ns	27 $\phi$ max	$I_F = I_{RP} = 500\text{mA}$ 75% Recovery point, $T_j = 25^{\circ}\text{C}$
5	Thermal Resistance	$R_{th(j-c)}$	$^{\circ}\text{C} / \text{W}$	$\phi$ 4 $\phi$ max.	Between Junction and case

6. Characteristics

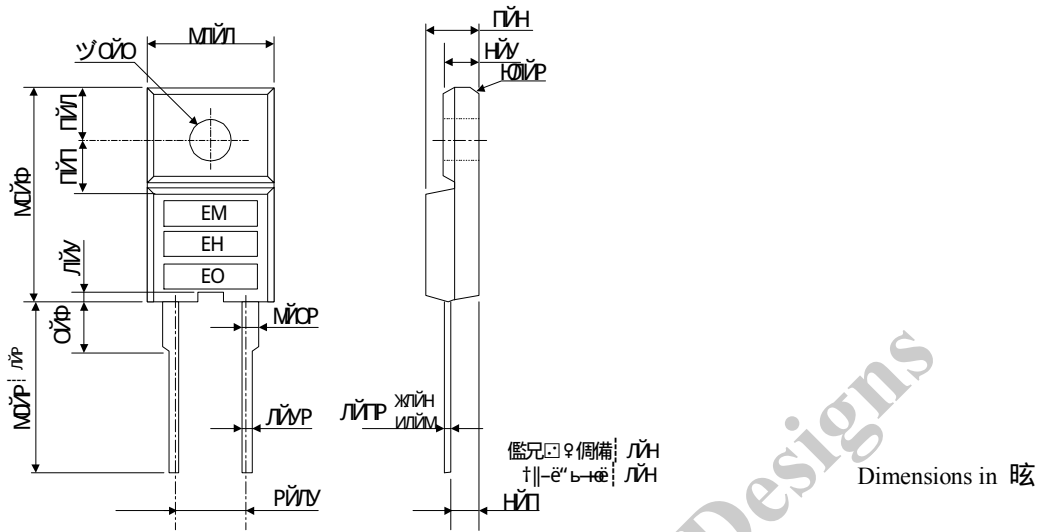


7. Derating



8. Package information

8-1 Package type, physical dimensions and material



8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking

Type Name	Marking		
	*1φ Type Name	*2φ Polarity	*3φ Lot number
FMXK-1086S	XK1086	S	1st letter: Last digit of year 2nd letter: Monthφ From 1 to 9 for Jan. to Sep., O for Oct., N for Nov., D for Dec. 3rd & 4th letter: Day ex. 8N21φ (Nov. 21, 2008)